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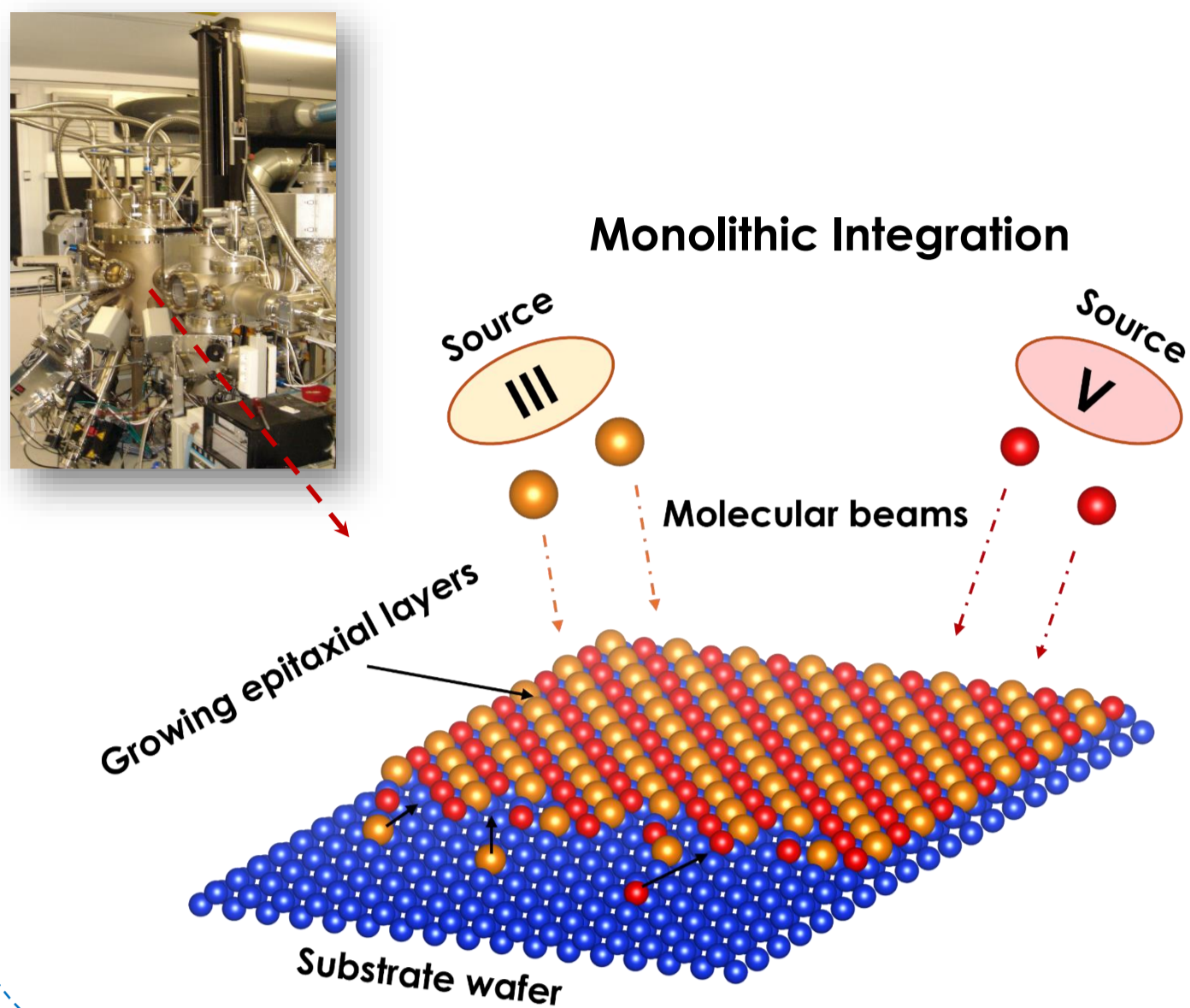
Impact of initial surface passivation on wetting properties analysis during III-V/Si epitaxy

S. Pallikkara Chandrasekharan^{1,*}, D. Gupta¹, C. Cornet¹, L. Pedesseau¹

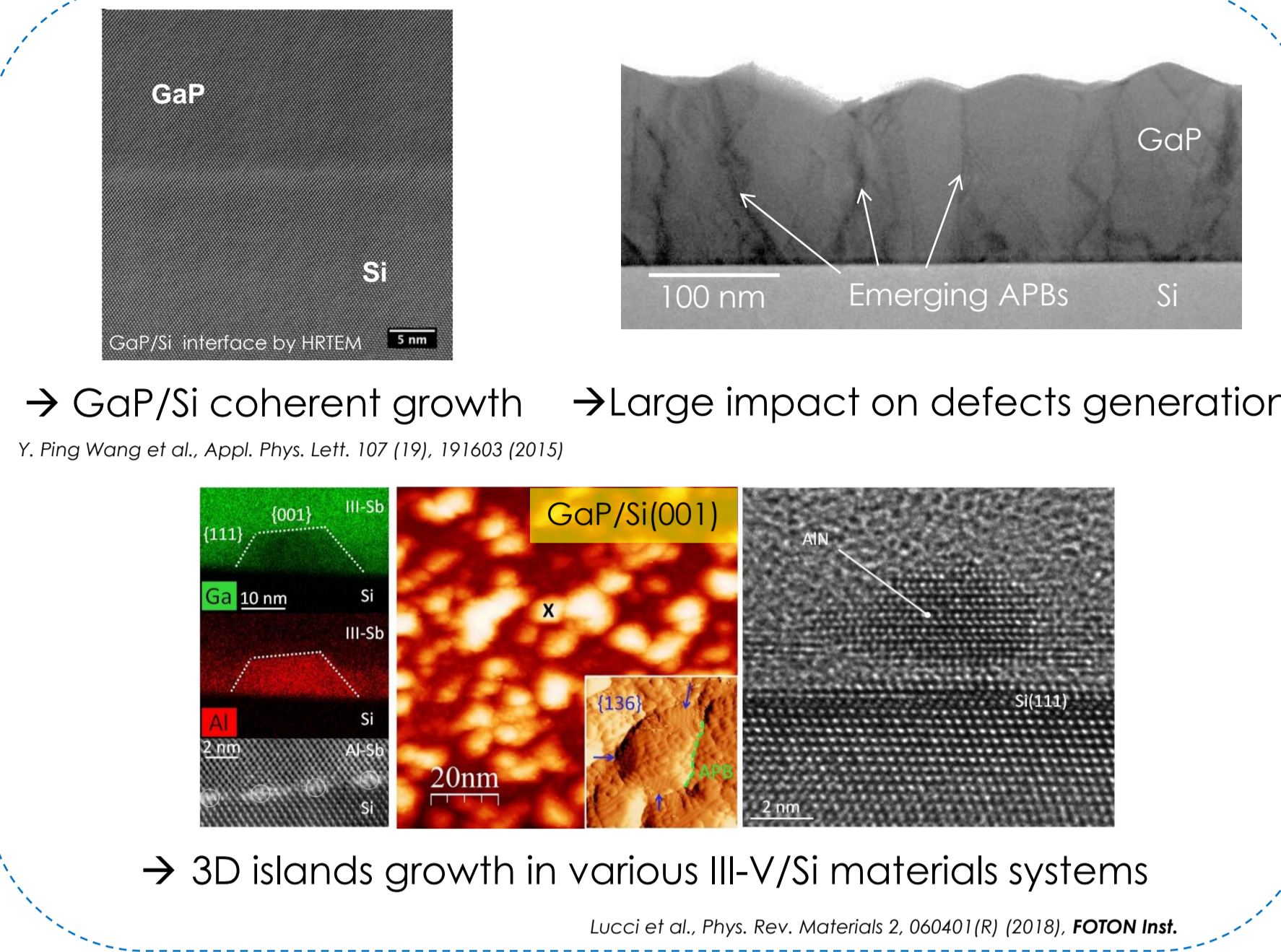
(1) Univ Rennes, INSA Rennes, CNRS, Institut FOTON-UMR 6082, F-35000, Rennes, France.

Introduction

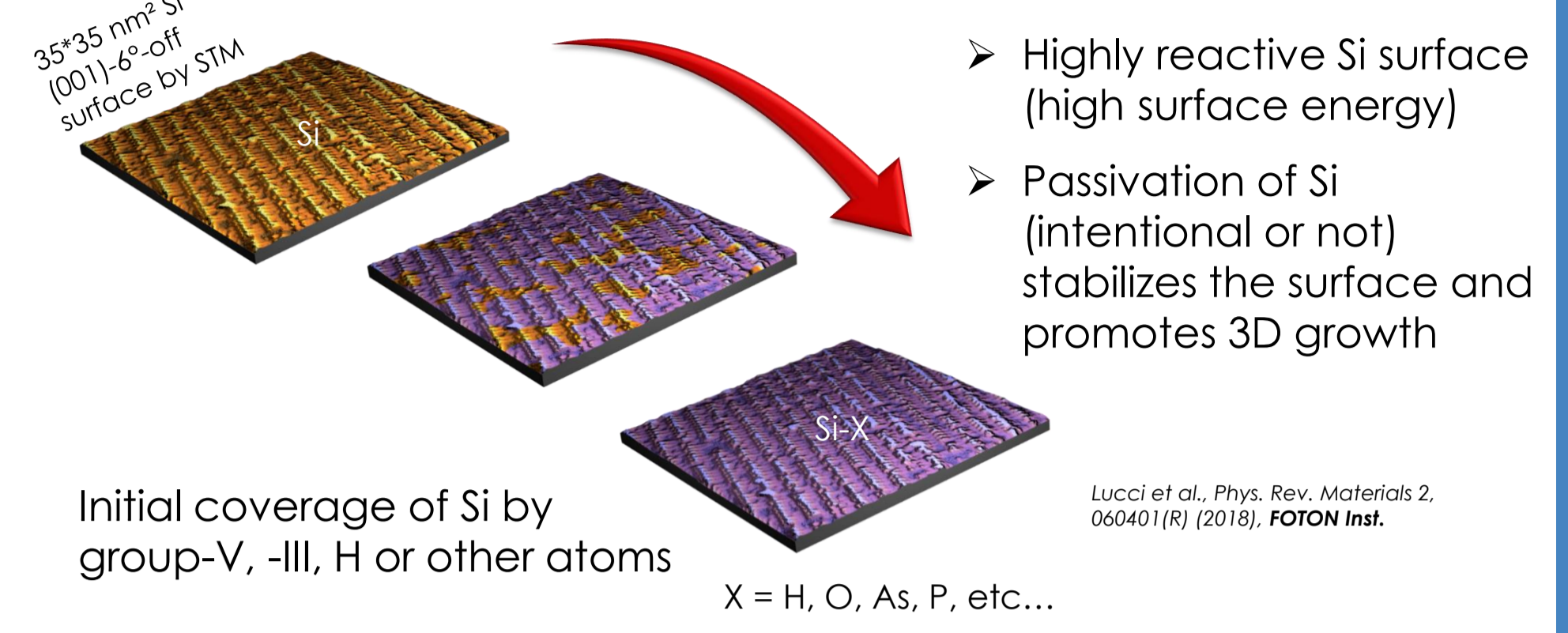
Molecular beam epitaxy



Experimental observations



Objectives

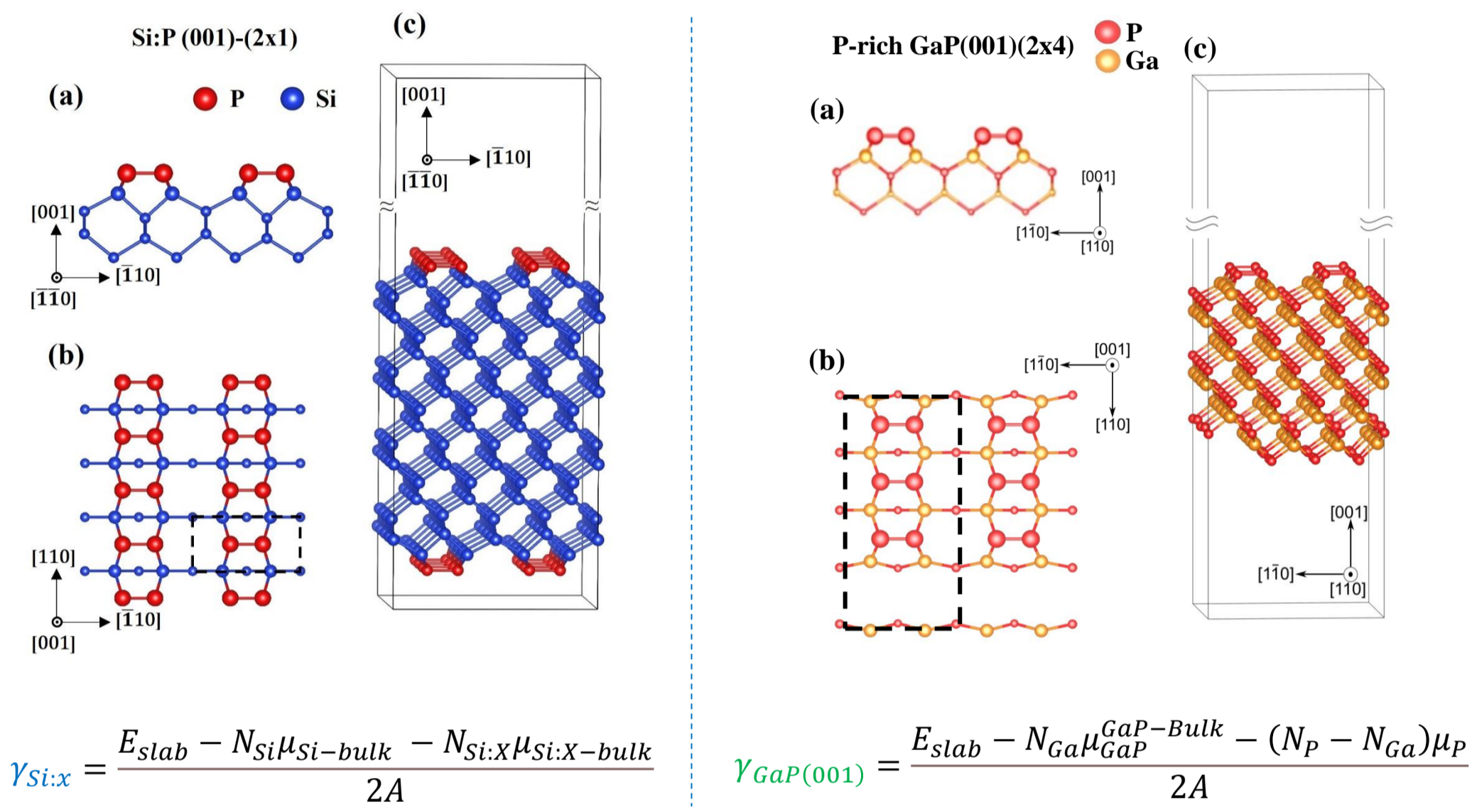


Spreading parameter (solid wetting theory)...

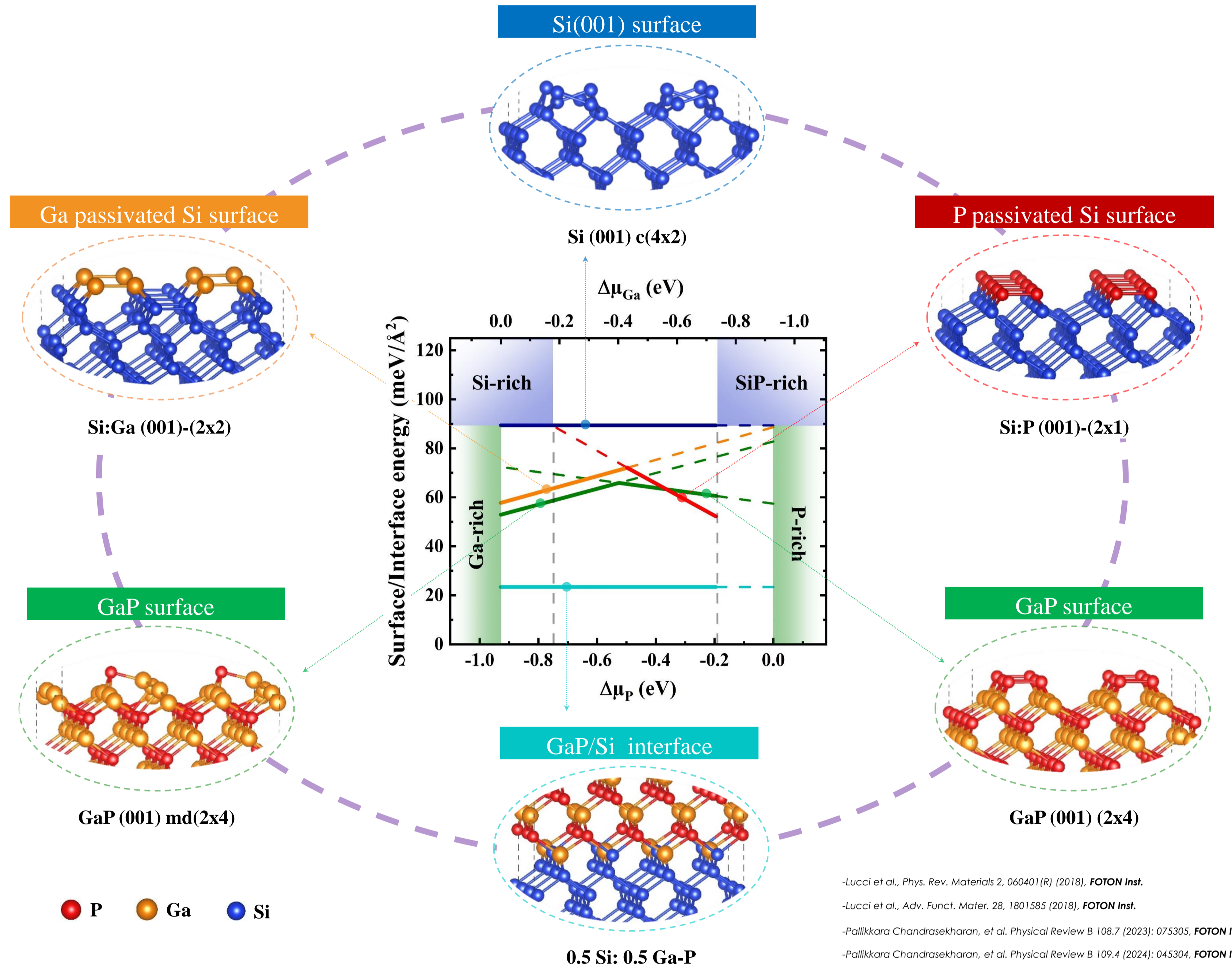
$$\Omega = \gamma^S_{(Si-x)} - \gamma^S_{(III-V)} - \gamma^I_{(III-V/Si)}$$

$\Omega > 0$, complete wetting
 $\Omega < 0$, partial wetting

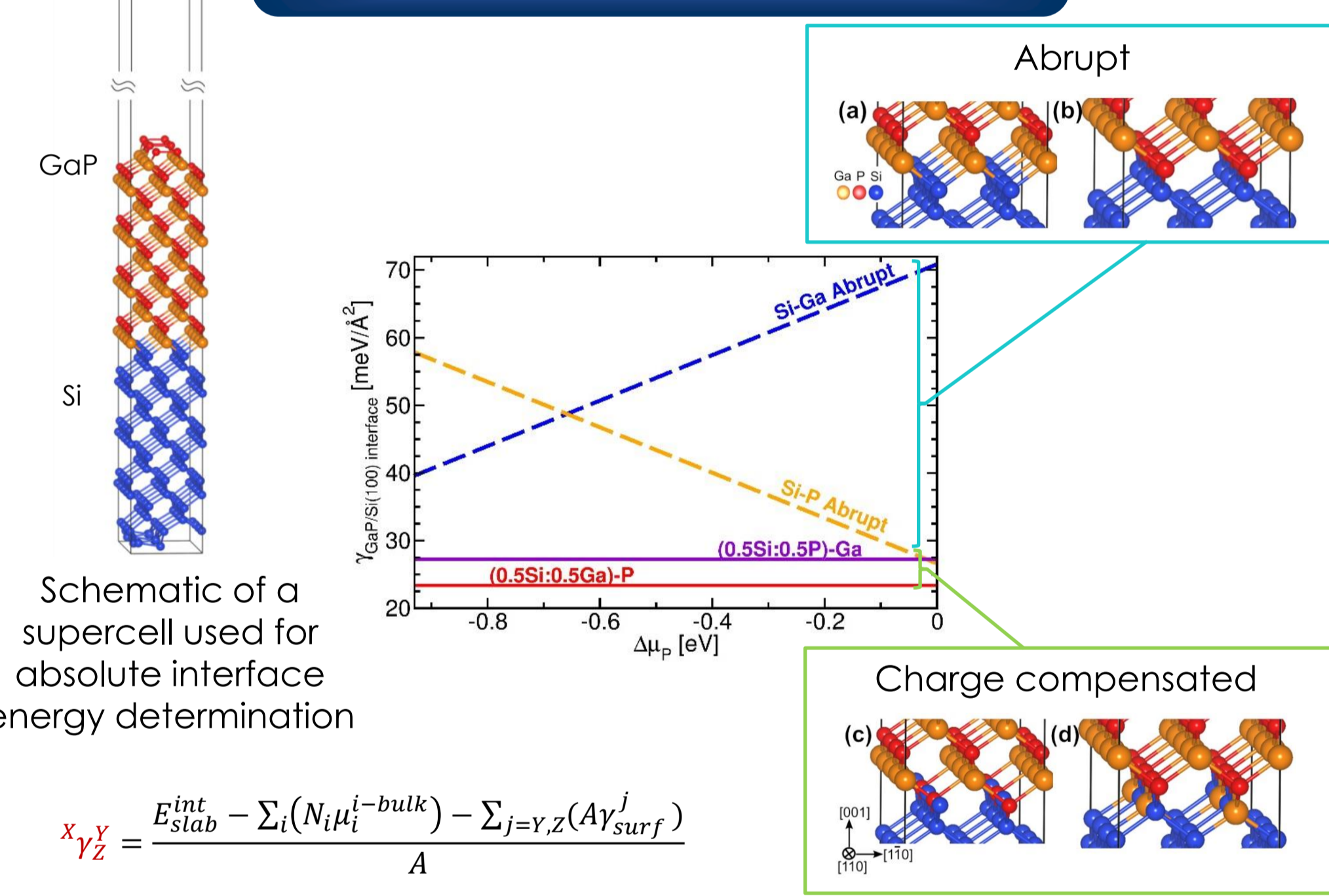
Absolute surface energies



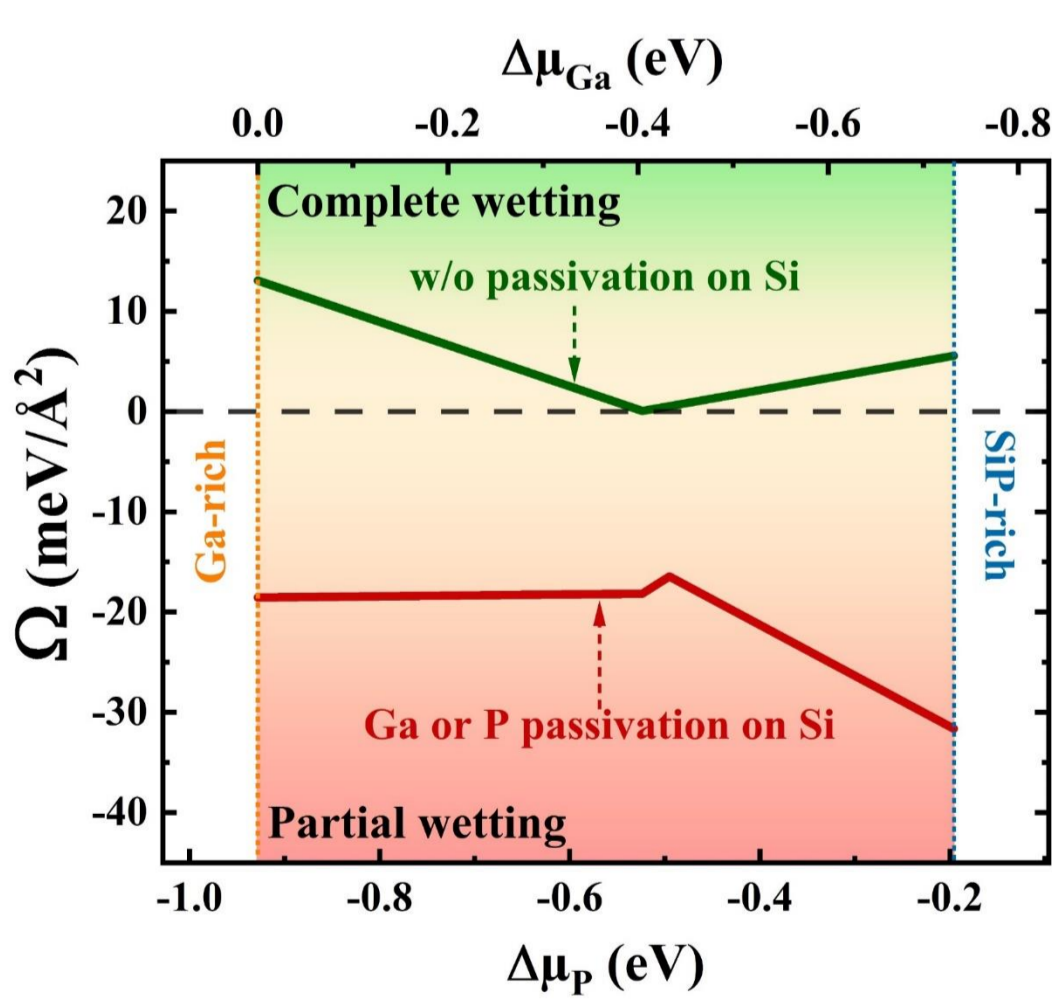
Surface and interface energies vs chemical potentials for GaP/Si



Absolute interface energies

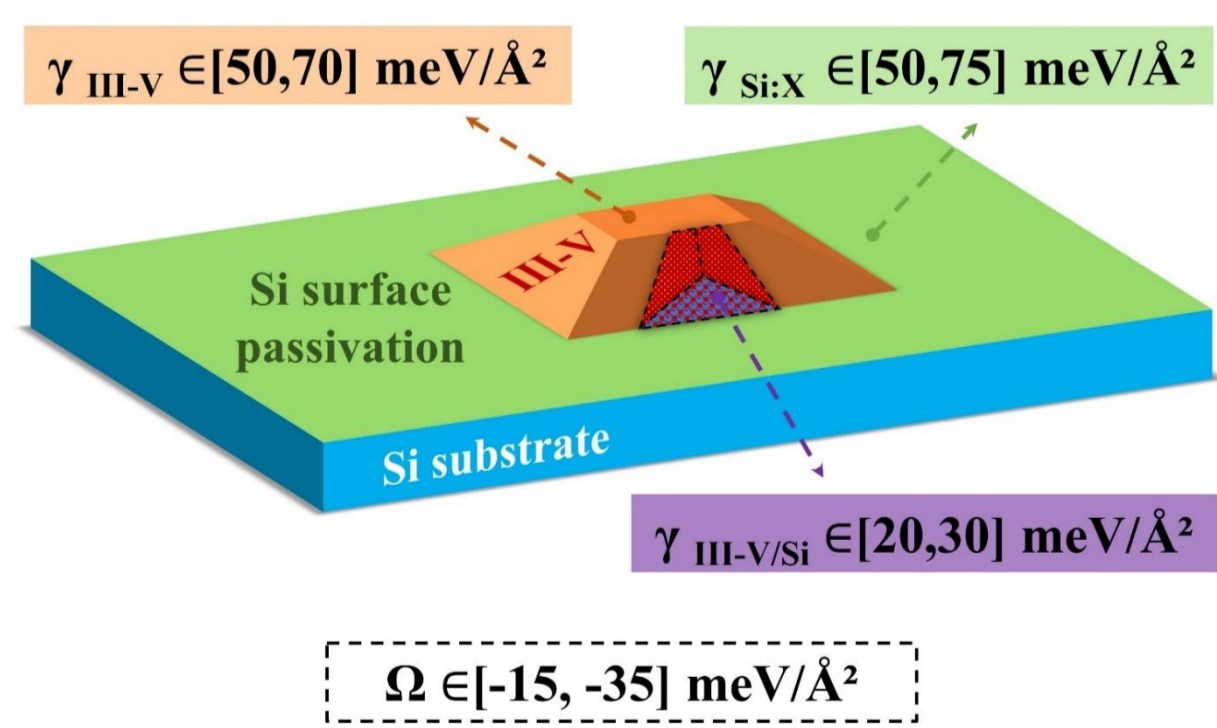


Wetting properties



Young-Dupré spreading parameter Ω

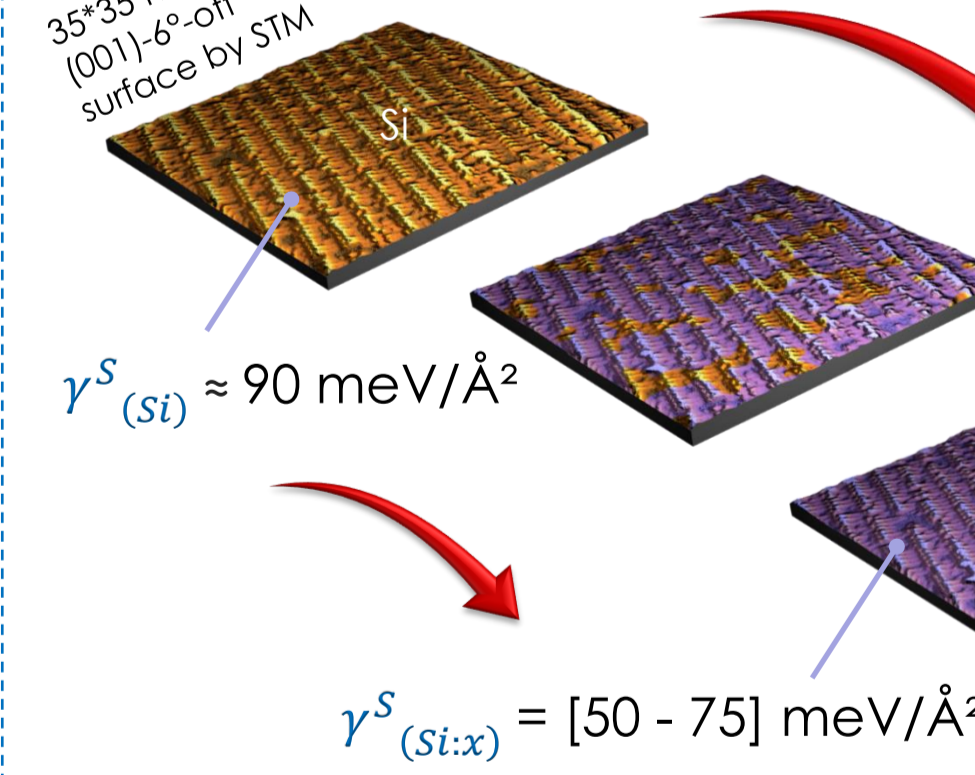
- Passivation promotes partial wetting conditions.



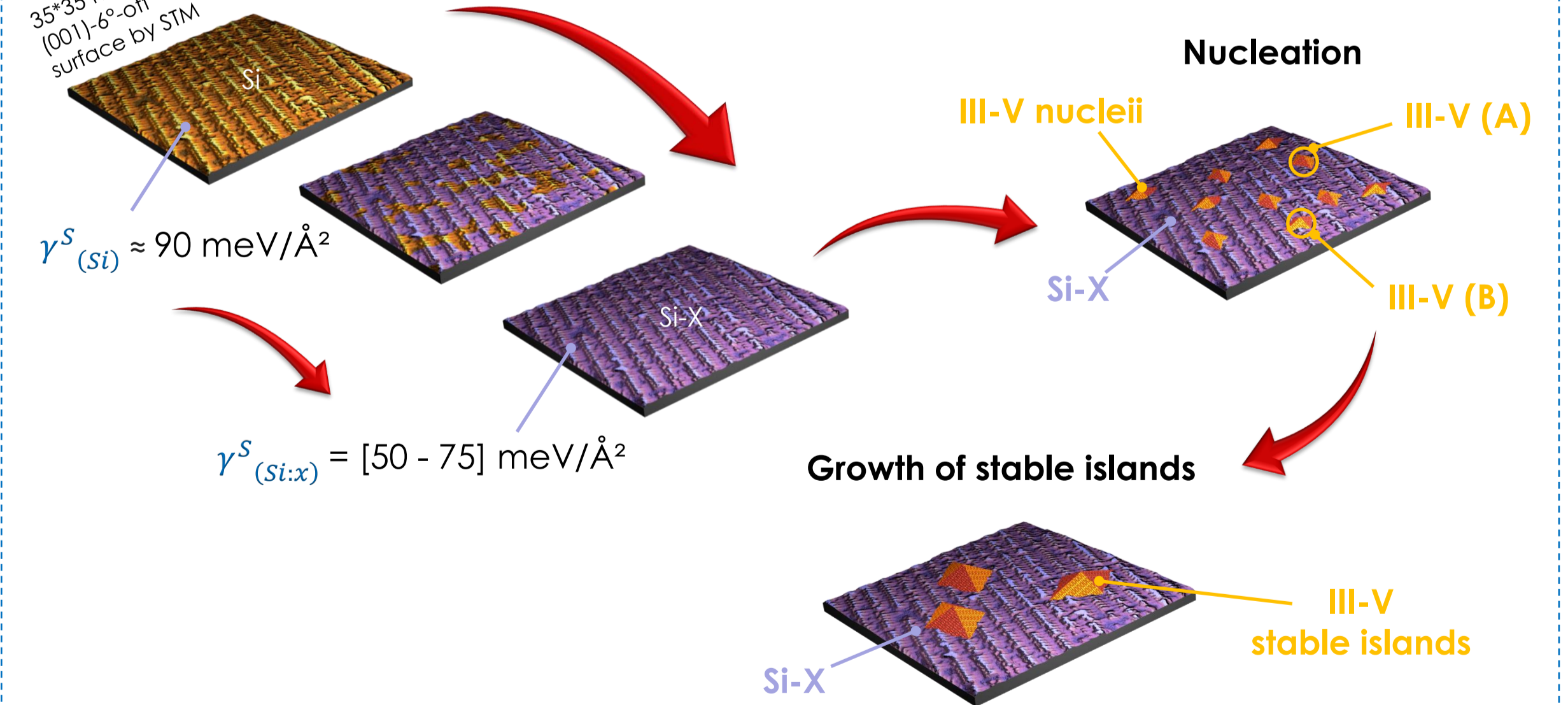
"Illustration summarizing the energies involved in the 3D island formation of GaP on the Si substrate with a range of possible energy values"

- Stable surface and interface energies support the growth of 3D islands.

Initial surface passivation



Proposed III-V/Si growth steps



Conclusions

- Inevitable passivation of Si prior to GaP/Si heteroepitaxy leads to a large decrease of the substrate surface energy.
- This decrease leads to a significant reduction in the spreading parameter.
- Destabilizing a passivated Si surface by at least 15 meV/\AA^2 or stabilizing the III-V (001) surface makes a complete wetting situation possible.
- Si passivation is a driving force for the formation of 3D stable islands, which leads to the emergence of structural defects due to their coalescence.

Acknowledgements

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